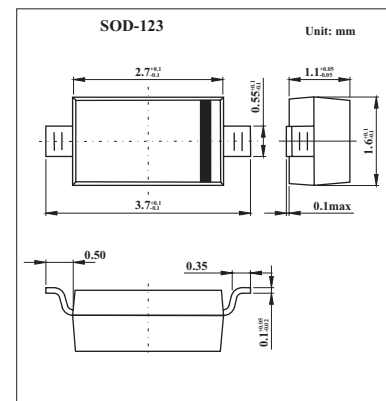


Variable Capacitance Diode for VCXO

HVD359

■ Features

- High capacitance ratio and good C-V linearity.
- To be usable at low voltage.
- Super small Flat Lead Package (SFP) is suitable for surface mount design.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Value	Unit
Reverse Voltage	V _R	15	V
Junction temperature	T _j	125	°C
Storage temperature	T _{stg}	-55 to +125	°C

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Conditions	Min	Max	Unit
Reverse current	I _{R1}	V _R = 10 V		10	nA
	I _{R2}	V _R = 10 V, Ta = 60°C		100	
Capacitance	C ₁	V _R = 1 V, f = 1 MHz	24.8	29.8	pF
	C ₄	V _R = 4 V, f = 1 MHz	6	8.3	
Capacitance ratio	n	C ₁ / C ₄	3		
Series resistance	r _s	V _R = 4 V, f = 100 MHz		1.5	Ω
ESD-Capability *1		C = 200 pF, R = 0 Ω, Both forward and reverse direction 1 pulse.	80		V

Note:

1. Failure criterion ; I_R ≥ 20 nA at V_R = 10 V

■ Marking

Marking	G
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